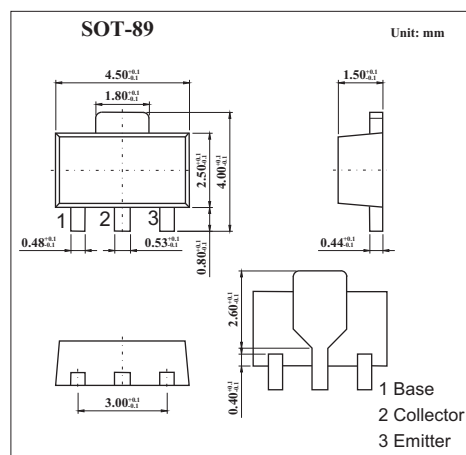


Epitaxial Planar PNP Transistor

KTA1663

Features

Collector Power Dissipation: $P_c=500\text{mW}$ Collector Current: $I_c=-1.5\text{A}$ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-30	V
Collector-Emitter Voltage	V_{CE0}	-30	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_c	-1.5	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_c	500	mW
	P_{c^*}	1	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ\text{C}$

* mounted on ceramic substrate (250mm² X 0.8t)Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_c=-1\text{mA}$, $I_E=0$	-30			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_c=-10\text{mA}$, $I_B=0$	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EB0}$	$I_E=-1\text{mA}$, $I_c=0$	-5.0			V
Collector Cut-off Current	I_{CB0}	$V_{CB}=-30\text{V}$, $I_E=0$			-100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=-5\text{V}$, $I_c=0$			-100	nA
DC Current Gain	h_{FE}	$V_{CE}=-2\text{V}$, $I_c=-500\text{mA}$	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=-1.5\text{A}$, $I_B=-0.03\text{A}$			-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-2\text{V}$, $I_c=-500\text{mA}$			-1.0	V
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$			50	pF
Transition Frequency	f_r	$V_{CE}=-2\text{V}$, $I_c=-500\text{mA}$		120		MHz

hFE Classification

Marking	HO	HY
Rank	O	Y
Range	100 200	160 320